Customer No.: 31561
Application No.: 10/708,016
Docket No.: 12030-US-PA

AMENDMENTS

To the Claims:

1. (previously presented) A pixel structure, adapted to be disposed on a substrate, comprising:

a scan line, disposed on the substrate;

a data line, disposed on the substrate;

an active element, disposed near to an intersection of the scan line and the data line on the substrate, and electrically coupled to the scan line and the data line;

a capacitor electrode, disposed on the substrate;

a pixel electrode, disposed over the capacitor electrode and electrically coupled to the active element, wherein the pixel electrode and the capacitor electrode form a pixel storage capacitor; and

an electrical field shielding layer, disposed between the data line and the pixel electrode; and

a transparent capacitor electrode with the capacitor electrode disposed between the transparent capacitor electrode and the pixel electrode, wherein the capacitor electrode, the transparent capacitor electrode and the pixel electrode form the pixel storage capacitor, and the capacitor electrode is made from a transparent material.

2. (original) The pixel structure of claim 1, wherein the active element comprises a low temperature polysilicon thin film transistor.

3. (original) The pixel structure of claim 2, further comprising a drain/source conductive layer, wherein the active element is electrically coupled to the data line and the pixel electrode through the drain/source conductive layer.

4. (currently amended and withdrawn) The pixel structure of claim 2, further comprising a conductive layer, wherein the active element is electrically coupled to the data line through the ~~drain/source~~ conductive layer, and the pixel electrode is directly electrically coupled to the active element.

5. (withdrawn) The pixel structure of claim 4, wherein the conductive layer is indium tin oxide or indium zinc oxide.

Claim 6 (canceled)

7. (previously presented) The pixel structure of claim 1, wherein the active element is directly electrically coupled to the transparent capacitor electrode.

8. (previously presented and withdrawn) The pixel structure of claim 1, wherein the active element is electrically coupled to the transparent capacitor electrode through the pixel electrode.

9. (previously presented) The pixel structure of claim 1, wherein the transparent capacitor electrode is made from indium tin oxide or indium zinc oxide.

Claims 10-11. (canceled)

12. (original) The pixel structure of claim 1, wherein the capacitor electrode, the electrical field shielding layer and the pixel electrode are made from indium tin oxide or indium zinc oxide.

Claims 13-25. (canceled).